PROCESS CPD87R

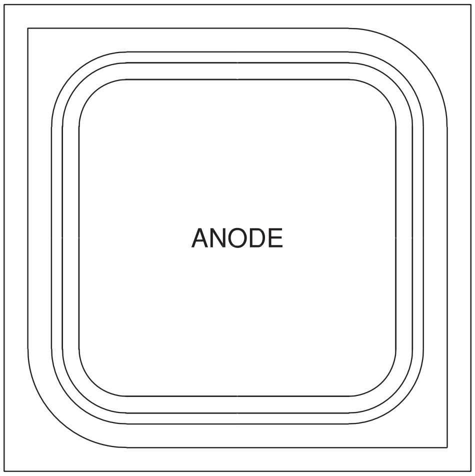
Schottky Diode

Low Leakage Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.6 x 14.6 MILS
Die Thickness	3.9 MILS
Anode Bonding Pad Area	11.8 x 11.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 5 INCH WAFER
80,698

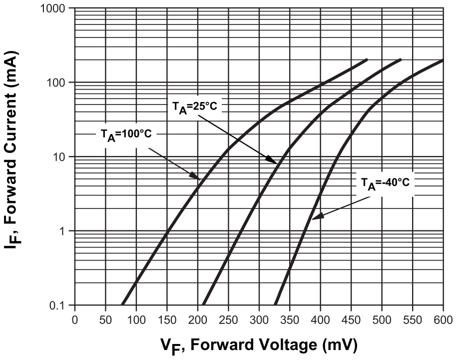
PRINCIPAL DEVICE TYPES
CFSH2-4L

R1 (22-March 2010)

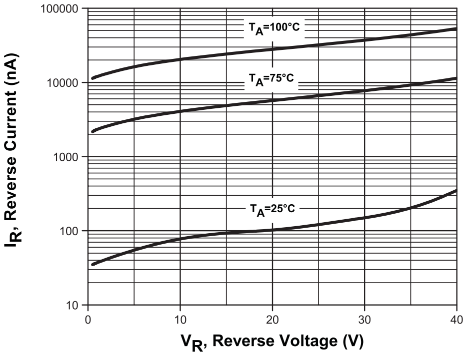
PROCESS CPD87R

Typical Electrical Characteristics

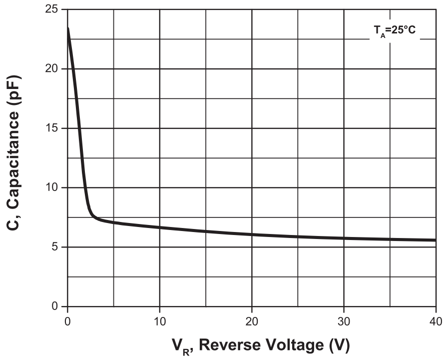
Forward Voltage



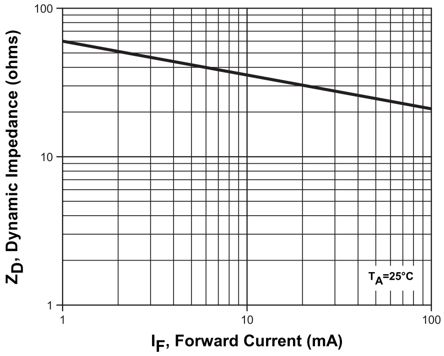
Leakage Current



Capacitance



Forward Dynamic Impedance



Normalized Power Derating